

Quantum transport in twisted bilayer graphene

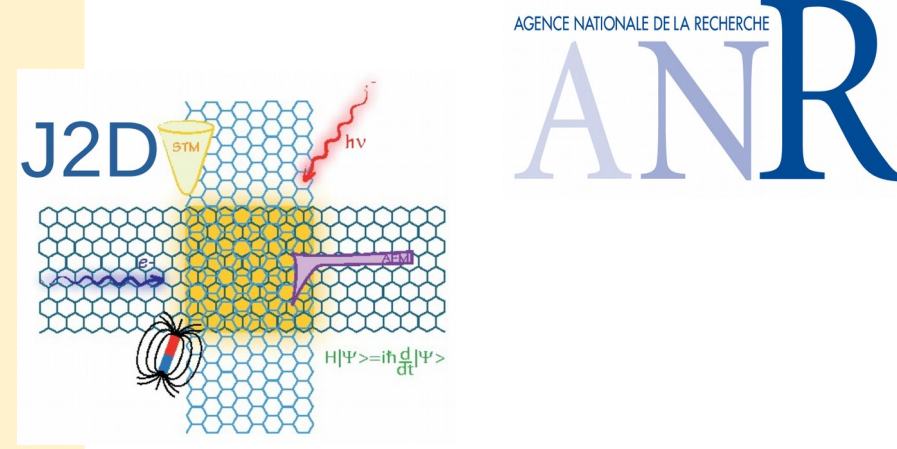
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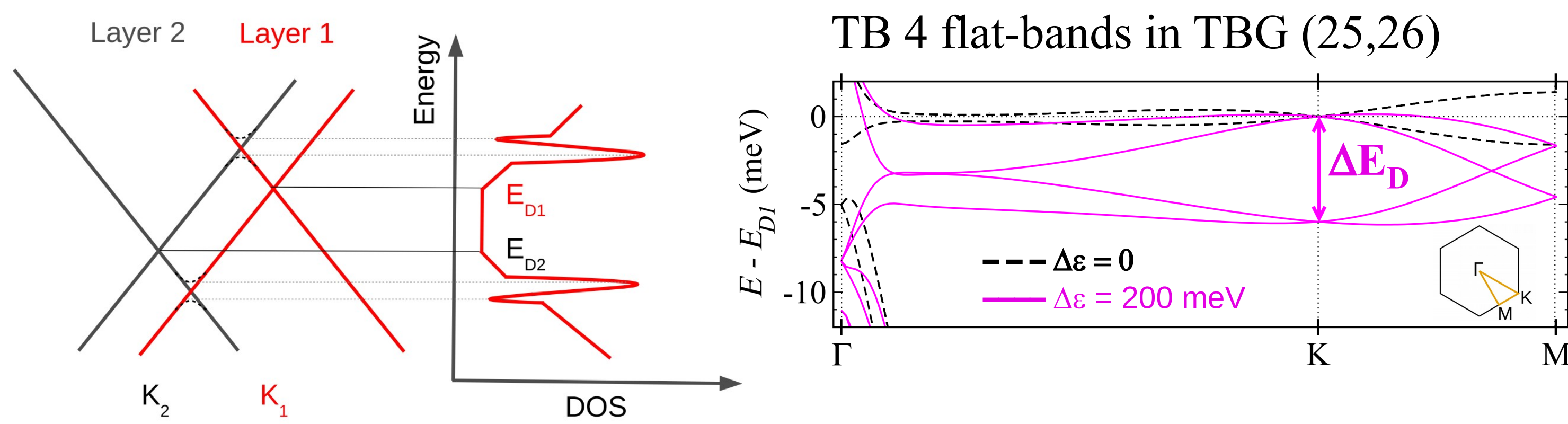


ABSTRACT: It has been shown theoretically and experimentally that twisted bilayer graphene (TBG), forming Moiré patterns, confine electrons in a tunable way as a function of the rotation angle [1-3]. The discovery of correlated insulators and superconductivity in 2018 [3] at so-called “magic angles” has stimulated an avalanche of experimental and theoretical activities. In the framework of the **Kubo-Greenwood formula for the conductivity**, we present **tight-binding (TB) calculations of quantum diffusion properties** in TBG at various rotation angles θ [4,5]. We analyze in particular the effect of **static defects**, the effect of and **electric bias**. One of the main results is that **flat-bands induce a breakdown of the standard Boltzmann theory of transport**.

This **anomalous quantum transport in flat-bands** can exist in other systems like **Quasicrystals** [6] and **flat-bands induced by defects in graphene** [7,8].

Effect of an electric bias on bands [4]

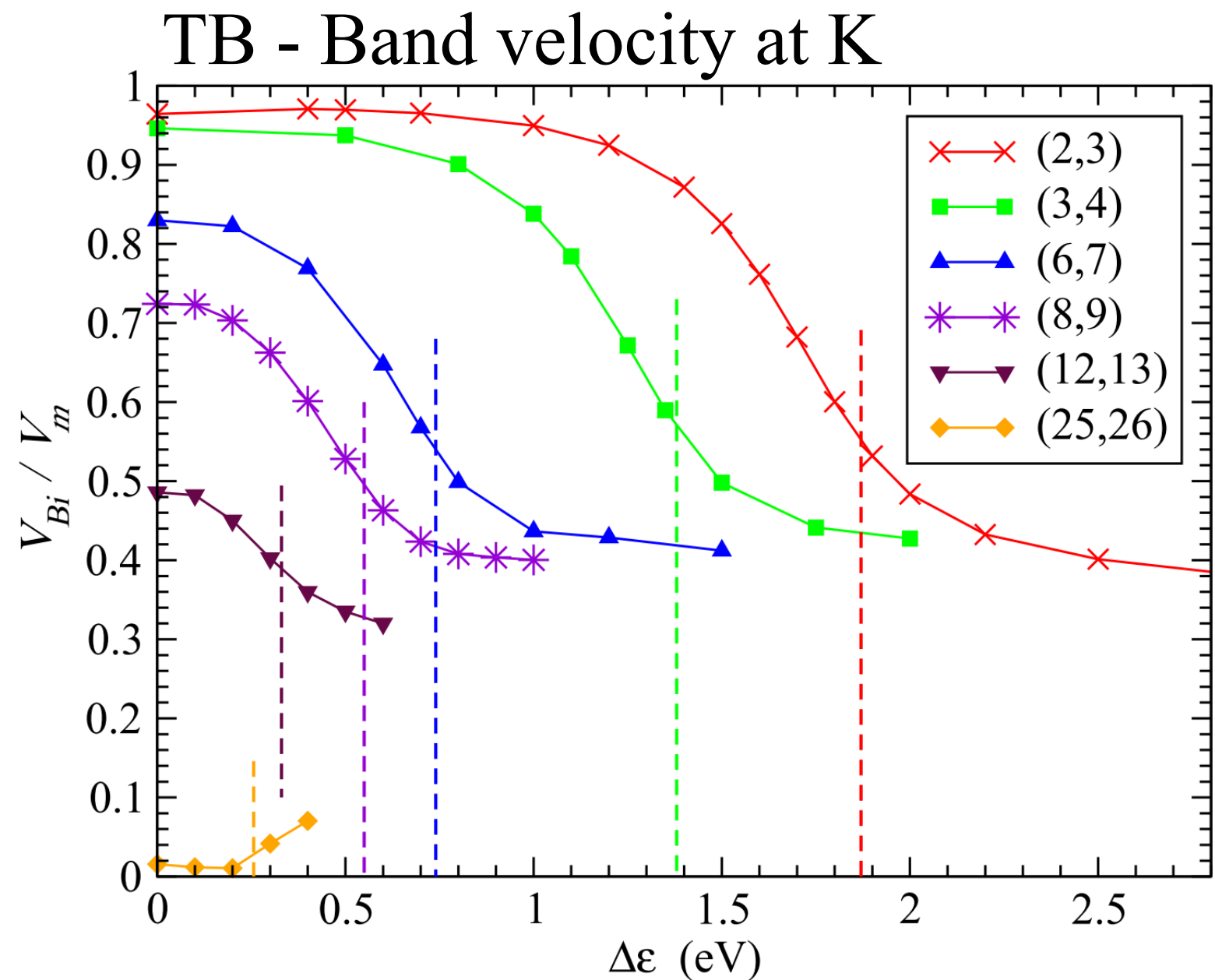
A difference $\Delta\varepsilon$ between the on-site energies of layer 1 and layer 2
 \Rightarrow Difference ΔE_D between the two corresponding Dirac energies



Twisted bilayer graphene (TBG) with various rotation angle θ

(n, m)	θ (°)	N
(1, 3)	32.20	52
(5, 9)	18.73	604
(2, 3)	13.17	76
(3, 4)	9.43	148
(6, 7)	5.08	508
(8, 9)	3.89	868
(12, 13)	2.65	1876
(15, 16)	2.13	2884
(25, 26)	1.30	7804
(33, 34)	0.99	13468

N: number of atoms in a Moiré cell



\Rightarrow **Reduction of band velocity by bias potential**

Microscopic conductivity (static defects) [5]

Microscopic conductivity σ_M is a good estimation of room temperature conductivity (without quantum corrections)

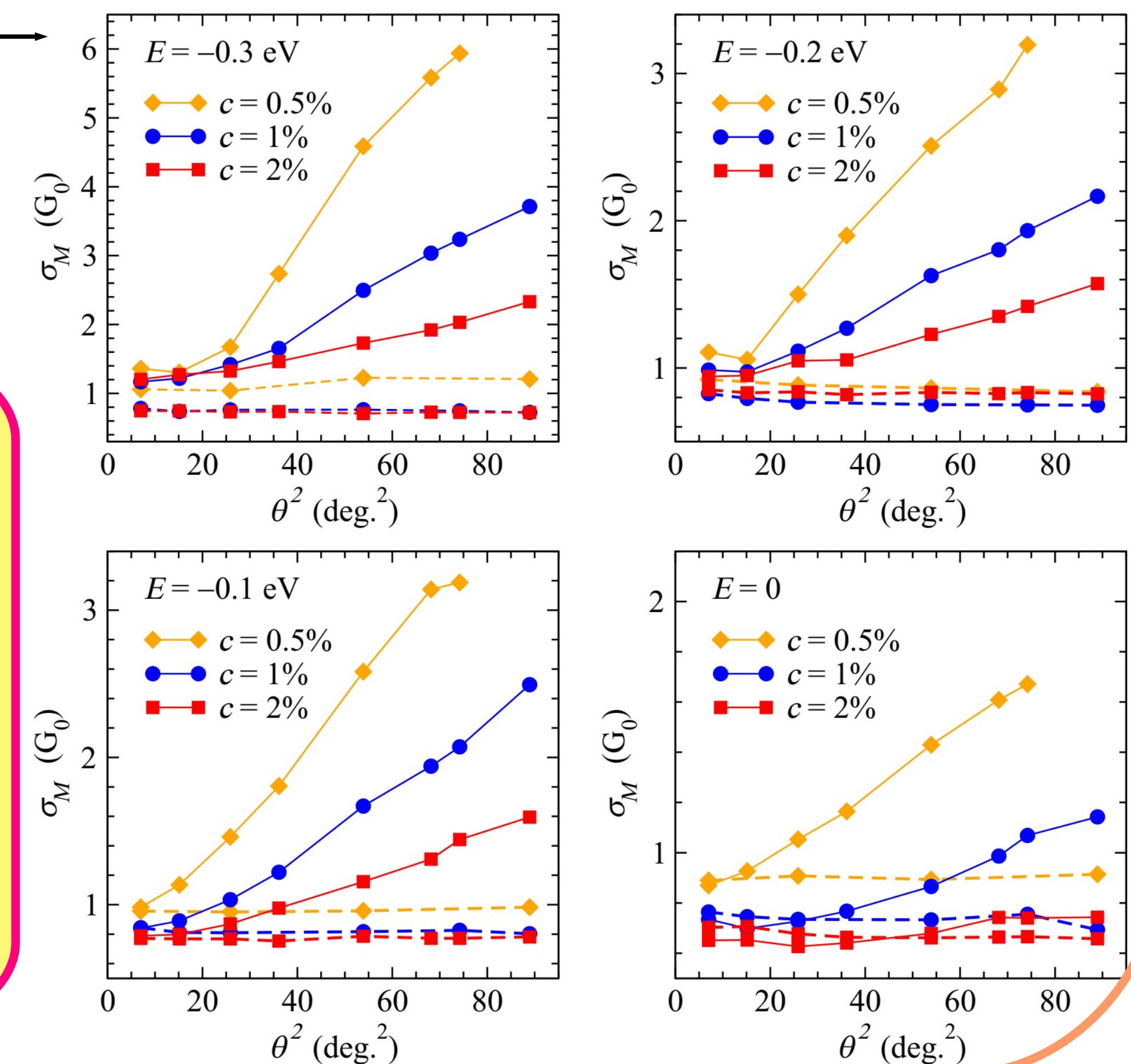
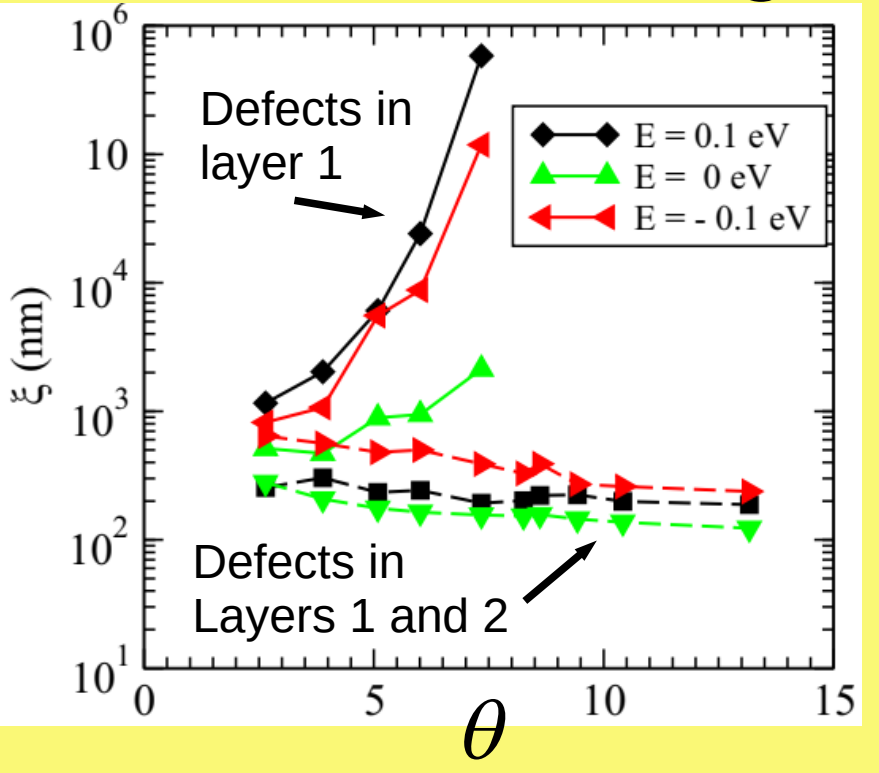
With defects (vacancies) located in layer 2 only:

Continuous model: $\sigma_M(E) \simeq \sigma_{M,MLG} \left(1 + \frac{\rho_1(E) \theta^2}{\rho_2(E) \theta_0^2} \right)$ ρ_i : DOS layer i , $\theta_0 \simeq 2^\circ$

TB calculations:

For Fermi energy E closed to Dirac energy ($E_D = 0$), σ_M is almost linear with θ^2 .

At low temperature: quantum corrections \Rightarrow localization length



Quantum diffusion: Boltzmann and non-Boltzmann terms [4]

Kubo-Greenwood dc-conductivity $\sigma_{xx}(E_F, \tau) = \frac{e^2}{S} n(E_F) D(E_F, \tau)$

Diffusivity $D(E_F, \tau) = \frac{1}{2\tau^2} \int_0^\infty \Delta X^2(E_F, t) e^{-t/\tau} dt$

Relaxation time approximation: Scattering time (defect or phonon): τ

Mean square spreading: $\Delta X^2(E, t) = \langle (X(t) - X(0))^2 \rangle_E$

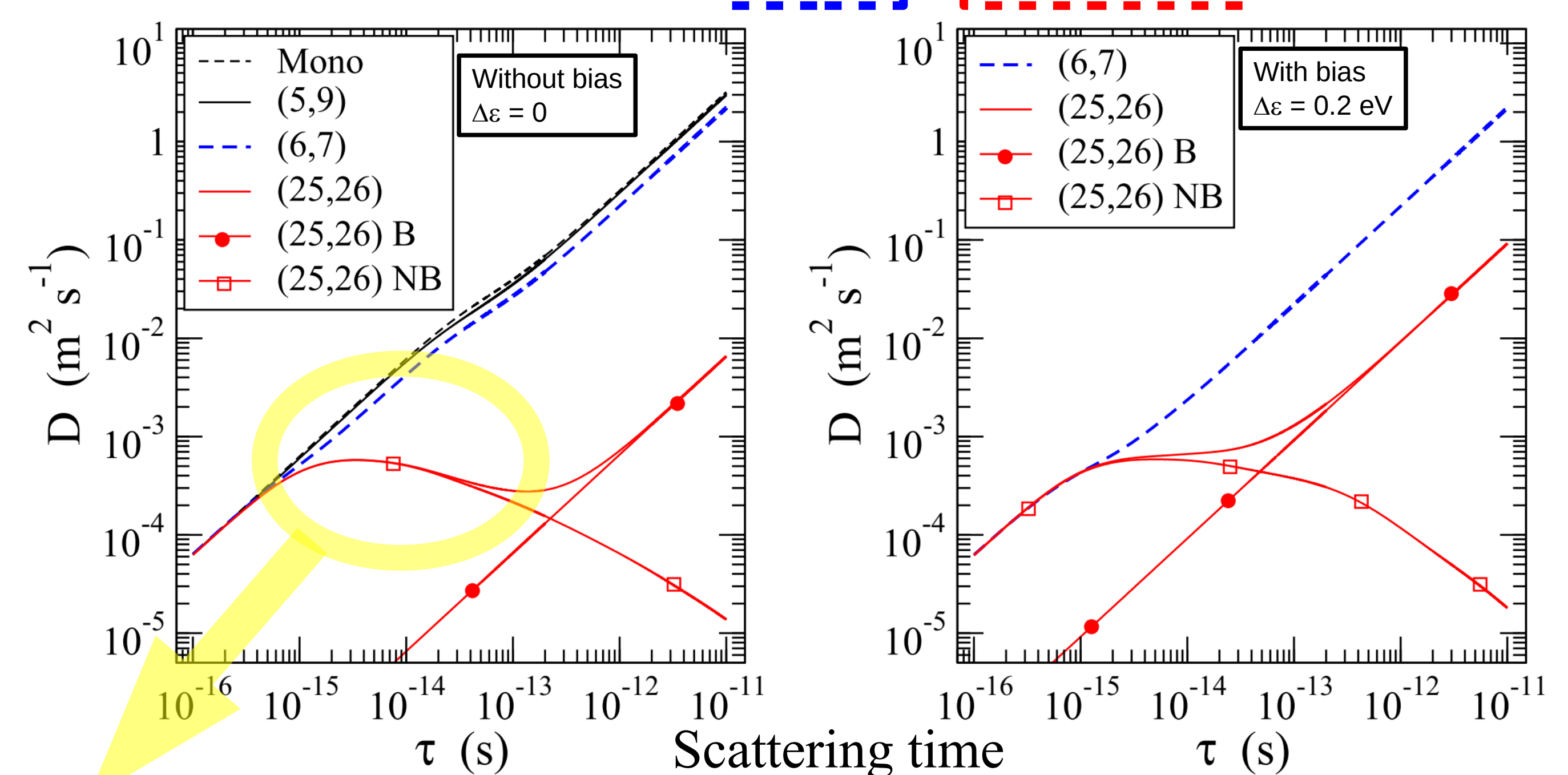
$$\Delta X^2(E, t) = 2\hbar^2 \left\langle \sum_{n'} \left[1 - \cos \left(\frac{(E_n - E_{n'})t}{\hbar} \right) \right] \frac{|\langle n\vec{k} | V_x | n'\vec{k} \rangle|^2}{(E_n - E_{n'})^2} \right\rangle_{E_n=E} = V_B^2 t^2 + \Delta X_{NB}(E, t)$$

Velocity: $V_x = \frac{1}{i\hbar} [X, H]$ \rightarrow Diagonal terms (Boltzmann): intra-bands
 \rightarrow Non diagonal terms (Non Boltzmann): inter-bands

\Rightarrow For Twisted Bilayer Graphene (25,26), $\theta = 1.3^\circ$, close to magic angle, **Non-Boltzmann terms dominate in the conductivity**

Diffusivity of the 4 flat-bands of the Moiré (half-filling)

$$D(E_F, \tau) = D_B(\tau) + D_{NB}(E_F, \tau)$$



SUMMARY: \triangleright A applied bias potential –or and an asymmetric doping between the two layers– reduces the velocity of Dirac-bands in TBG
 \triangleright **Conductivity** of TBG, with an asymmetric distribution of states defects between the two layers, **varies like θ^2**
 \triangleright **Non-Boltzmann terms (inter-band hopping terms)** dominate in the quantum diffusion in flat-bands in TBG

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